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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10.098,706	03 15 2002	Rama I. Hegde	SC11697TP	2984
23125 73	690 07 10 2003			
MOTOROLA INC AUSTIN INTELLECTUAL PROPERTY LAW SECTION 7700 WEST PARMER LANE MD: TX32/PL02 AUSTIN, TX 78729			EXAMINER	
			SARKAR, ASOK K	
			ART UNIT	PAPER NUMBER
			2829	
			DATE MAILED: 07/10/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	10/098,706	HEGDE ET AL.				
Office Action Summary	Examiner	Art Unit				
	Asok K. Sarkar	2829				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	ely filed s will be considered timely. the mailing date of this communication.				
1) Responsive to communication(s) filed on 11 J	une 2003 .					
<u> </u>	s action is non-final.					
3) Since this application is in condition for allowa		osecution as to the merits is				
closed in accordance with the practice under E Disposition of Claims	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.				
4) Claim(s) <u>1-3,9,26,27 and 29</u> is/are pending in t	the application.					
4a) Of the above claim(s) is/are withdraw	n from consideration.					
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>1-3,9,26,27 and 29</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/or election requirement.						
Application Papers						
9) The specification is objected to by the Examiner						
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11) ☐ The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved by the Examiner.						
If approved, corrected drawings are required in rep	·					
12) The oath or declaration is objected to by the Exa	aminer.					
Priority under 35 U.S.C. §§ 119 and 120						
13) Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 119(a)	-(d) or (f).				
a) ☐ All b) ☐ Some * c) ☐ None of:						
 Certified copies of the priority documents 	have been received.					
Certified copies of the priority documents	have been received in Application	on No				
 3. Copies of the certified copies of the priori application from the International Burn * See the attached detailed Office action for a list of 	eau (PCT Rule 17.2(a)).	C				
14) Acknowledgment is made of a claim for domestic	·					
a) The translation of the foreign language prov		,				
15) Acknowledgment is made of a claim for domestic						
Attachment(s)						
Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal P	(PTO-413) Paper No(s) atent Application (PTO-152)				
Patent and Trademark Office	S	Dod of Day, No. 5				

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DETAILED ACTION

Response to Arguments

1. Applicant's arguments with respect to claims 1 – 3, 9, 26, 27 and 29 have been considered but are most in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 112

- 2. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter, which the applicant regards as his invention.
- 3. Claims 1 3, 9, 26, 27 and 29 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. The use of the term adjacent may also mean the layers are side by side although the figures show them to be a stack. The use of an indefinite term renders the claims indefinite. For the examination purpose, the adjacent was considered to be over.

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. Claims 1 3 and 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Halliyal, US 6,451,641 or Ballantine, US 6,444,592 or Haukka, US 2002/0115252 in view of Shinriki, US 5,292,673.

Regarding these claims Halliyal teaches a transistor device 100 in which the gate

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dielectric 108 is present between the semiconductor substrate 102 and the gate electrode 110 (see Fig. 1) in which HfO_2 (first layer) and ZrO_2 (second layer) and other dielectric layer (third layer) are used as multiple layers (see column 6, line 37 and column 7, lines 3 – 7).

Ballantine teaches transistor device with gate dielectric layer 14 between gate electrode and the substrate in which HfO_2 (first layer) and ZrO_2 (second layer) and other dielectric layer (third layer) are used as multilayers (see column 4, lines 20 – 23).

Haukka teaches transistor device with gate dielectric layer 14 between gate electrode and the substrate in which HfO₂ (first layer) and ZrO₂ (second layer) and other dielectric layer (third layer) are used as multilayers (see paragraphs 25, 27 and 56).

Halliyal or Ballantine or Haukka teaches the formation of high – k dielectric materials which can be formed by combining or using composite materials but fails to teach that HfO₂ is adjacent to the gate electrode and ZrO₂ is adjacent to the semiconductor substrate.

Shinriki teaches that these high – k materials can be used either in stack or mixture to obtain the similar effect of other high – k materials in between column 8, line 66 and column 9, line 5.

Therefore, it would have been obvious to one with ordinary skill in the art at the time of the invention to modify Hailiyai or Bailantine or Haukka by using a layered dielectric of HfO₂ and ZrO₂ in which HfO₂ is adjacent to the gate electrode and ZrO₂ is adjacent to the semiconductor substrate since Shinriki teaches that the same high – k effect can be obtained irrespective of using them in layers or in mixtures and therefore

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will provide the designed high dielectric constant and excellent mobility and can therefore be used in the order in which HfO_2 is adjacent to the gate electrode and ZrO_2 is adjacent to the semiconductor substrate.

6. Claims 26, 27 and 29 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shinriki, US 5,292,673 and Haukka, US 2002/0115252.

Regarding claimd 26 and 27, Shinriki teaches a transistor device comprising a semiconductor substrate 1 having a source and drain 6 and a channel between the source and the drain; a gate electrode 5 over the channel and a gate dielectric 4 with respect to Fig. 5.

Shinriki teaches that gate dielectric can consist of HfO₂, ZrO₂ and other oxide can be used either in stack or mixture to obtain the similar effect of other high – k materials in between column 8, line 66 and column 9, line 5.

Haukka teaches transistor device with gate dielectric layer 14 between gate electrode and the substrate in which HfO₂ (first layer) and ZrO₂ (second layer) and other dielectric layer (third layer) are used as multilayers (see paragraphs 25, 27 and 56). See also Figs. 3 and 4.

Therefore, it would have been obvious to one with ordinary skill in the art at the time of the invention to use a layered dielectric of HfO₂ and ZrO₂ since Shinriki teaches that the same high – k effect can be obtained irrespective of using them in layers or in mixtures and therefore will provide the designed high dielectric constant and excellent mobility and a third layer such as Al₂O₃ can be used to provide diffusion barrier properties as taught by Haukka.

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Regarding claim 29, Note that a "product by process" claim is directed to the product per se, no matter how actually made, *In re Hirao*, 190 USPQ 15 at 17 (footnote 3). See also *In re Brown*, 173 USPQ 685; *In re Luck*, 177 USPQ 523; *In re Fessmann*, 180 USPQ 324; *In re Avery*, 186 USPQ 161; *In re Wertheim*, 191 USPQ 90 (209 USPQ 554 does not deal with this issue); *In re Marosi et al*, 218 USPQ 289; and particularly *In re Thorpe*, 227 USPQ 964, all of which make it clear that it is the patentability of the final product per se which must be determined in a "product by process" claim, and not the patentability of the process, and that an old or obvious product produced by a new method is not patentable as a product, whether claimed in "product by process" claims or not. Note that applicant has the burden of proof in such cases, as the above case law makes clear.

Additionally, Haukka teaches depositing ZrO₂ by the ALD process (see abstract, also see paragraph 97).

Conclusion

7. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the

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shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Asok K. Sarkar whose telephone number is 703 308 2521. The examiner can normally be reached on Monday - Friday (8 AM- 5 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Kammie Cuneo can be reached on 703 308 1233. The fax phone numbers for the organization where this application or proceeding is assigned are 703 308 7722 for regular communications and 703 308 7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703 308 4918.

Asok K. Sarkar June 26, 2003